

App. No. 09/196,185
Amendment Accompanying RCE dated March 6, 2006

Docket No. AB-1758 US

Amendments to the Specification

Please replace paragraph [0024] with the following amended paragraph:

[0024] A passivation layer 600 ~~[[700]]~~ is formed on the data wire 500, 510 and 520 and portions of the amorphous silicon layer 400 which is not covered by the data wire 500, 510 and 520. The passivation layer 600 ~~[[700]]~~ has a contact hole C1 exposing the drain electrode 520, and another contact hole C2 exposing the gate pad 230 along with the gate insulating layer 300. Here, the description of a data pad connected to the data line 500 is omitted.

Please replace paragraph [0025] with the following amended paragraph:

[0025] Finally, a pixel electrode 700 formed of ITO (indium tin oxide) and connected to the drain electrode 520 through a contact hole C1 is formed on the passivation layer 600 ~~[[700]]~~. Furthermore, a gate ITO layer 710 connected to the gate pad 230 through the contact hole C2 ~~[[720]]~~ and improving the contact characteristics is formed on the passivation layer 600 ~~[[700]]~~.

Please replace paragraph [0032] with the following amended paragraph:

[0032] Thereafter, exposed portions of the extrinsic amorphous silicon layer 411 are ~~[[is]]~~ removed such that the extrinsic amorphous silicon layer is then divided into two portions 410 and 420, and the central portion of the amorphous silicon layer 400 is exposed.

Please replace paragraph [0034] with the following amended paragraph:

[0034] Finally, an ITO layer is deposited and patterned to form a pixel electrode 700 connected to the drain electrode 520 through the contact hole C1 and a gate ITO layer 710 connected to the gate pad 230 through the contact hole C2, ~~[[720]]~~ as shown in FIG. 4F. Here, the etchant for the ITO layer comprises hydrochloric acid and nitric acid, which may penetrate along the crack of the passivation layer 600 or along the edges of

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the ITO wire 700 and 710, and then may reach the data wire 500, 510 and 520, and the gate pad 230.